

1. SGT
2. TOLT BMS
3. $T_j(\text{max}) = 175$
4. MOS EAS

Product Name	Package	Vds V	ID A	Vth V typ.	Rds10V mohm typ.	Rds10V mohm max.	Qg10V nC typ.	Tj	N/P
YJTL1D1G08H	TOLT	80	453	3	0.86	1.13	219	-55-175	N
YJTL1D7G10H	TOLT	100	340	2.6	1.28	1.7	166	-55-175	N
YJTL1D9G10H	TOLT	100	270	3	1.5	1.9	132.5	-55-175	N
YJTL2D4G10H	TOLT	100	207	2.9	2	2.4	94	-55-175	N

MOSFET

Rdson

MOSFET

Qg

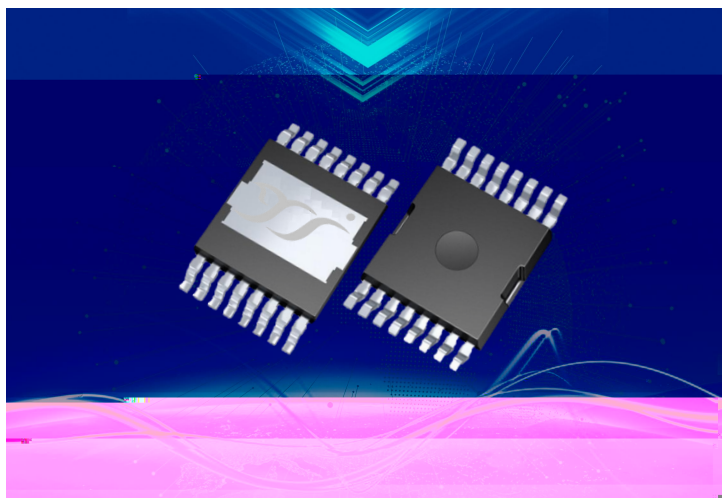
TOLT

SGT



BMS





Product Introduction

Yangjie Technology has recently launched a series of TOLT-packaged power MOSFET products for clean energy. These products adopt specially optimized SGT technology, featuring low on-resistance $R_{ds(on)}$ and gate charge Q_g , significantly reducing on-state and switching losses while enhancing the MOSFET's resistance to inrush current.

New Product Announcement

1. Adopting the optimized SGT process, the product features low internal resistance and excellent switching characteristics.
2. It adopts TOLT top heat dissipation packaging and is suitable for high-power applications such as BMS.
3. The working junction temperature $T_j(\max) = 175^\circ\text{C}$, with excellent heat dissipation performance and outstanding temperature rise performance.
4. Optimize the EAS capability of MOS products for various working conditions of industrial control applications to enhance the reliability of the products.

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BMS



Energy storage